

TOSHIBA Intelligent Power Module Silicon N Channel IGBT

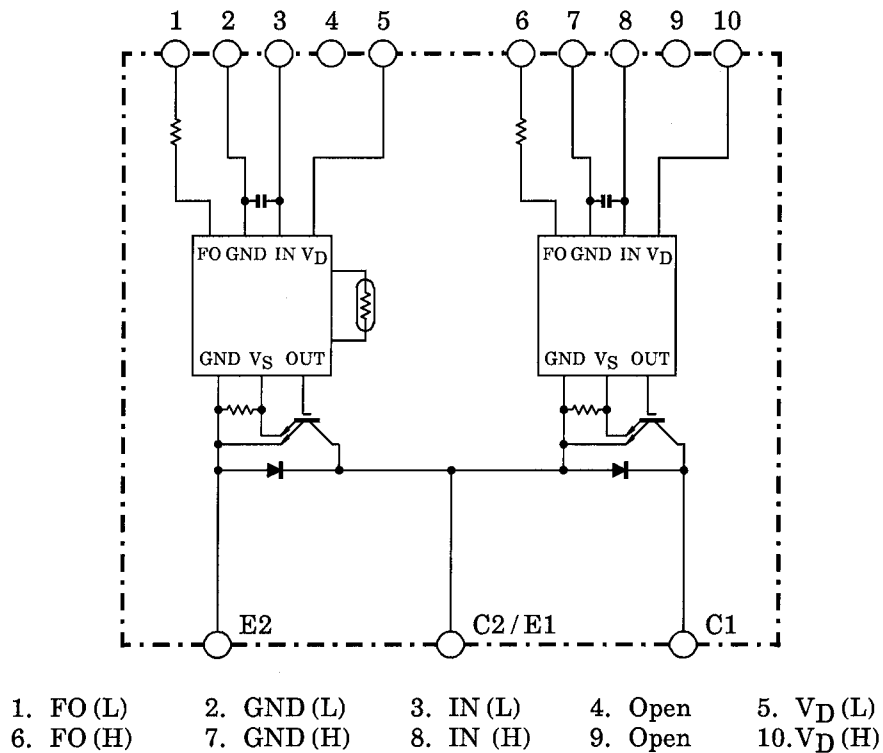
MIG300Q101H

High Power Switching Applications

Motor Control Applications

- Integrates inverter power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over temperature) in one package.
- The electrodes are isolated from case.
- Outline : TOSHIBA 2-110A1A
- Weight : 510g

Equivalent Circuit



Maximum Ratings ($T_j = 25^\circ\text{C}$)

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P–N power terminal	V_{CC}	900	V
	Collector–emitter voltage	—	V_{CES}	1200	V
	Collector current	$T_c = 25^\circ\text{C}$, DC	I_C	300	A
	Forward current	$T_c = 25^\circ\text{C}$, DC	I_F	300	A
	Collector power dissipation	$T_c = 25^\circ\text{C}$	P_C	1600	W
	Junction temperature	—	T_j	150	$^\circ\text{C}$
Control	Control supply voltage	V_D –GND terminal	V_D	20	V
	Input voltage	IN–GND terminal	V_{IN}	20	V
	Fault output voltage	FO–GND (L) terminal	V_{FO}	20	V
	Fault output current	FO sink current	I_{FO}	14	mA
Module	Operating temperature	—	T_C	$-20 \sim +100$	$^\circ\text{C}$
	Storage temperature range	—	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$
	Isolation voltage	AC 1 minute,	V_{ISO}	2500	V
	Screw torque	M6	—	3	N·m

Electrical Characteristics ($T_j = 25^\circ\text{C}$)

a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Typ.	Ma.	Unit
Collector cut-off current	I_{CEX}	$V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$	—	—	2	mA
			$T_j = 125^\circ\text{C}$	—	—	40	
Collector–emitter saturation voltage	$V_{CE}(\text{sat})$	$V_D = 15\text{V}$, $I_C = 300\text{A}$ $V_{IN} = 3\text{V} \rightarrow 0\text{V}$	$T_j = 25^\circ\text{C}$	—	2.7	2.5	V
			$T_j = 125^\circ\text{C}$	—	2.6	—	
Forward voltage	V_F	$I_F = 300\text{A}$		—	2.0	3.0	V
Switching time	t_{on}	$V_{CC} = 600\text{V}$, $I_C = 300\text{A}$ $V_D = 15\text{V}$, $V_{IN} = 3\text{V} \leftrightarrow 0\text{V}$ Inductive load (Note 1)		0.8	1.5	2.2	μs
	$t_{c(on)}$			—	0.5	1.0	
	t_{rr}			—	0.2	0.3	
	t_{off}			—	3.3	3.8	
	$t_{c(off)}$			—	0.4	0.8	

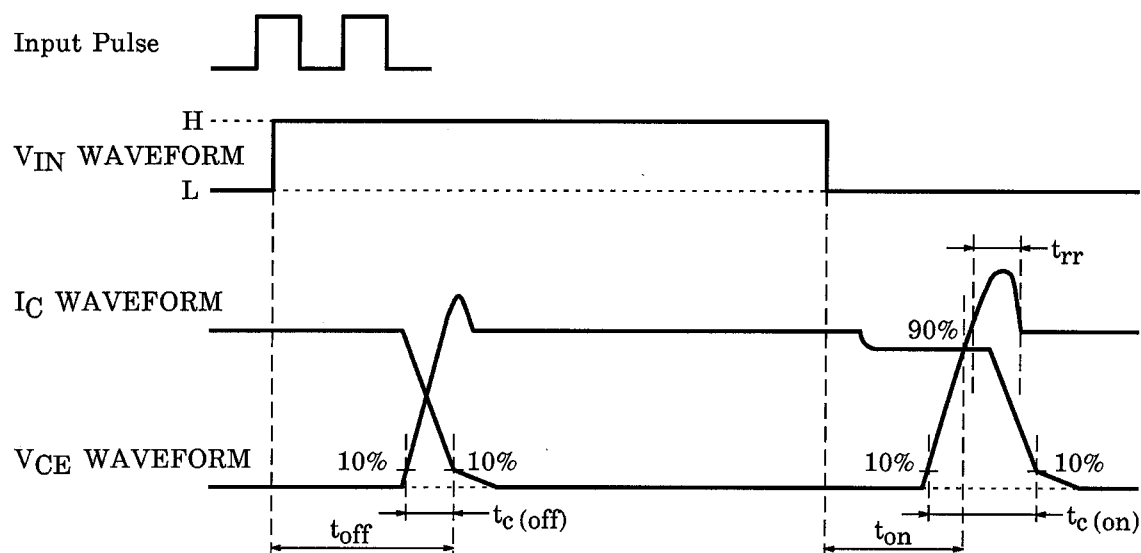
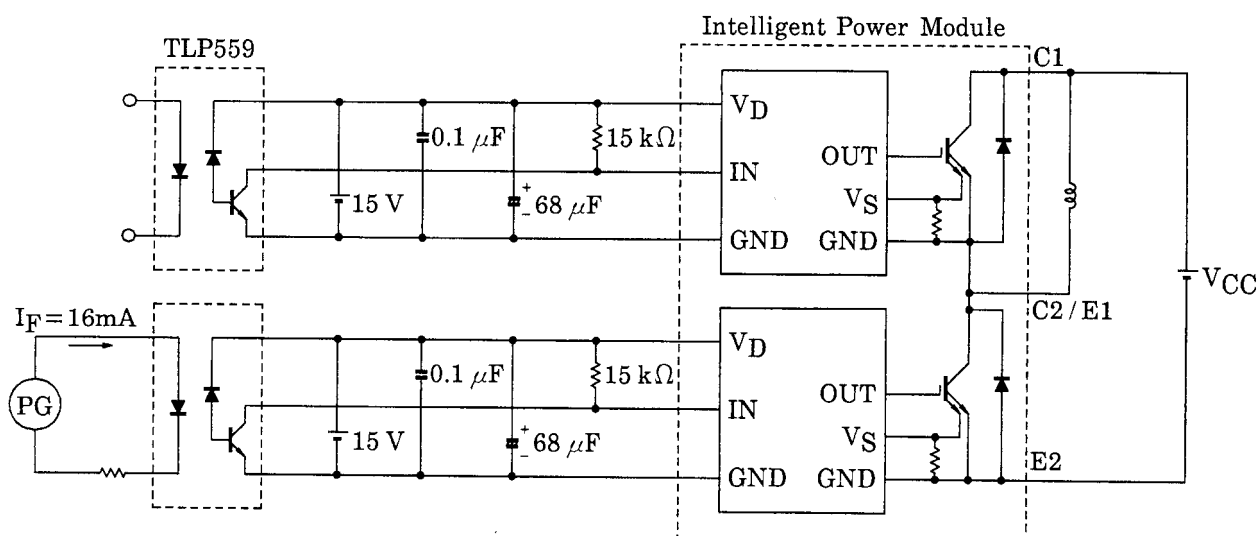
b. Control Stage ($T_j = 25^\circ\text{C}$)

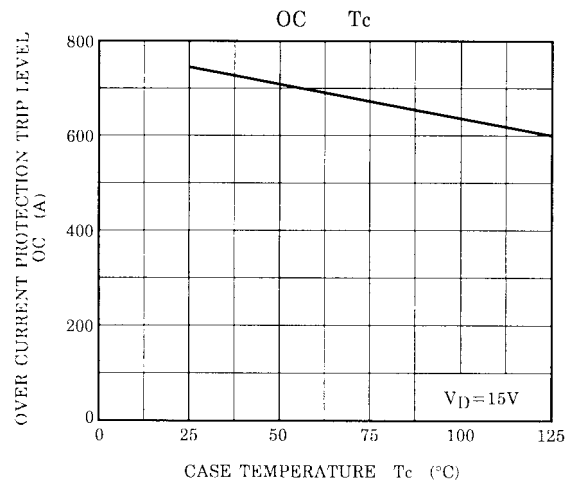
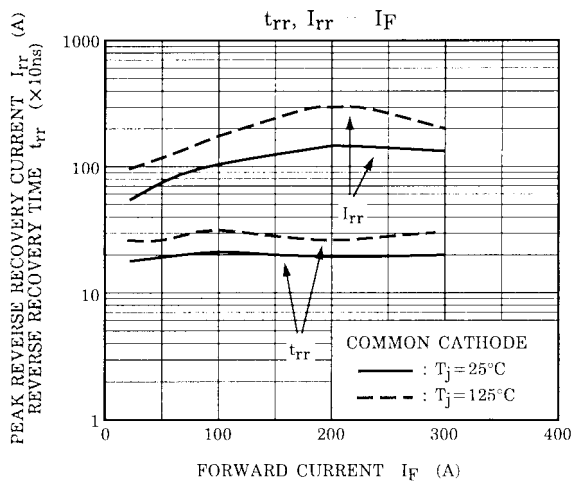
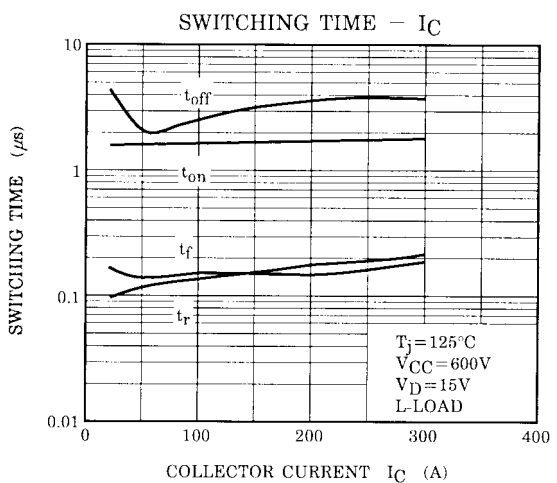
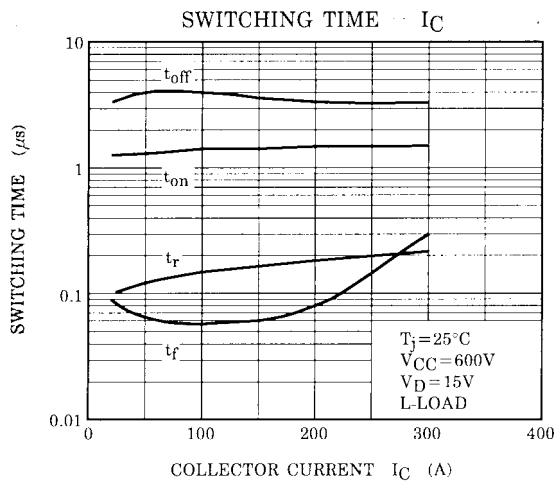
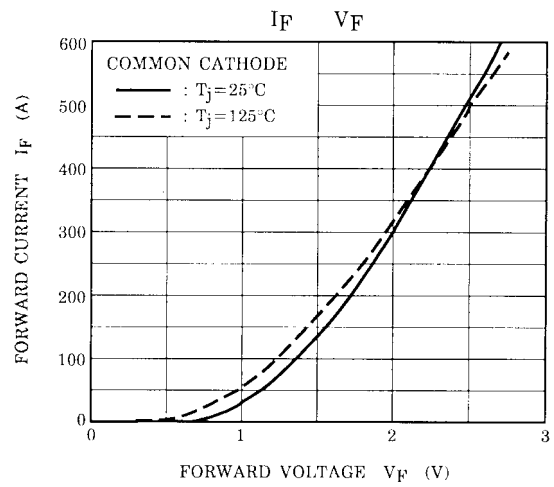
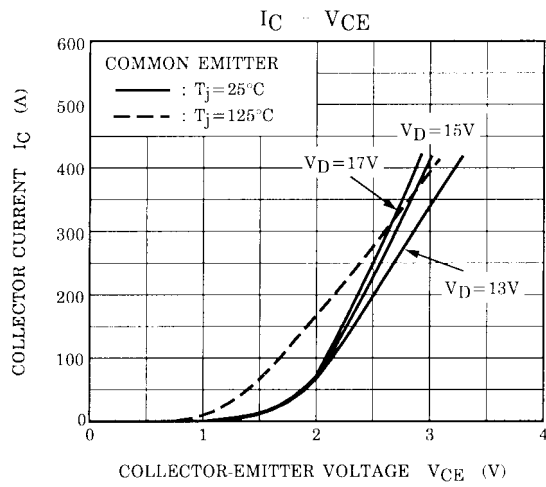
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Control circuit current		I_D	$V_D = 15\text{V}$	—	20	30	mA
Input on signal voltage		$V_{IN}(\text{on})$	$V_D = 15\text{V}$, $I_C = 300\text{mA}$	0.9	1.1	1.3	V
Fault output current	Protection	$I_{FO}(\text{on})$	$V_D = 15\text{V}$	8	10	12	mA
	Normal	$I_{FO}(\text{off})$		—	—	1	
Over current protection trip level		OC	$V_D = 15\text{V}$, $T_j = 125^\circ\text{C}$	420	600	—	A
Short circuit protection trip level		SC	$V_D = 15\text{V}$, $T_j = 125^\circ\text{C}$	630	900	—	A
Over current cut-off time		$t_{\text{off}}(\text{OC})$	$V_D = 15\text{V}$	—	10	—	μs
Over temperature protection	Trip level	OT	Case temperature	111	118	125	$^\circ\text{C}$
	Reset level	OTr		—	100	—	
Control supply under voltage protection	Trip level	UV	—	11.3	12.0	12.7	V
	Reset level	UVr		11.8	12.5	13.2	
Fault output pulse width		t_{FO}	$V_D = 15\text{V}$	1	2	3	ms

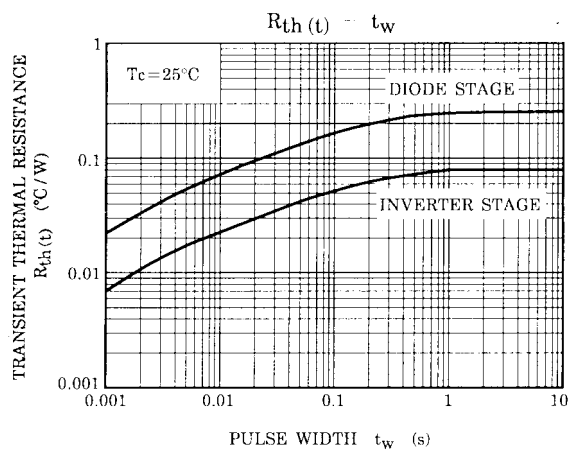
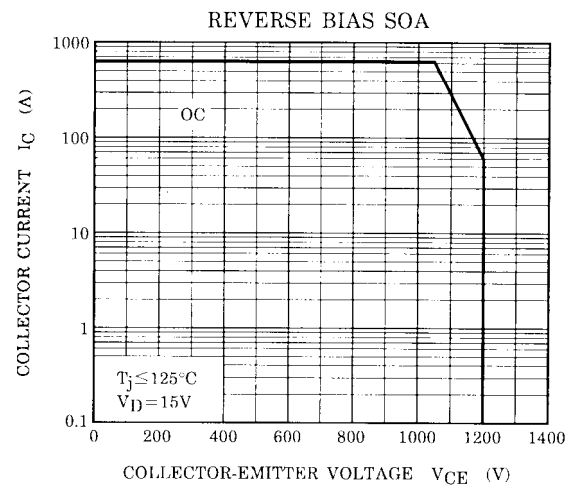
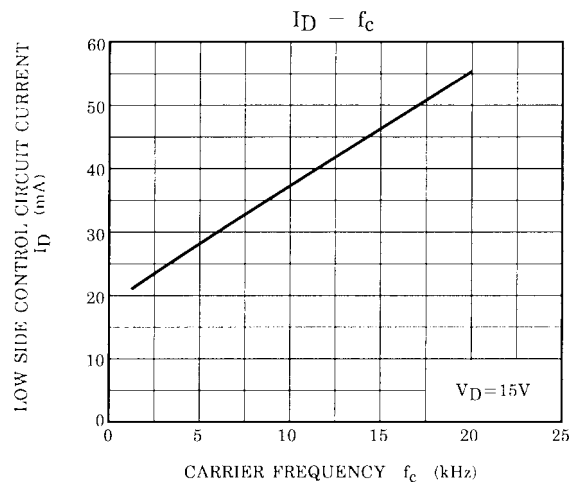
c. Thermal Resistance ($T_j = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Junction to case thermal resistance	$R_{th(j-c)}$	IGBT	—	—	0.078	$^\circ\text{C} / \text{W}$
		FRD	—	—	0.25	
Case to fin thermal resistance	$R_{th(c-f)}$	Compound is applied	—	0.03	—	$^\circ\text{C} / \text{W}$

Note 1: Switching time test circuit & timing chart

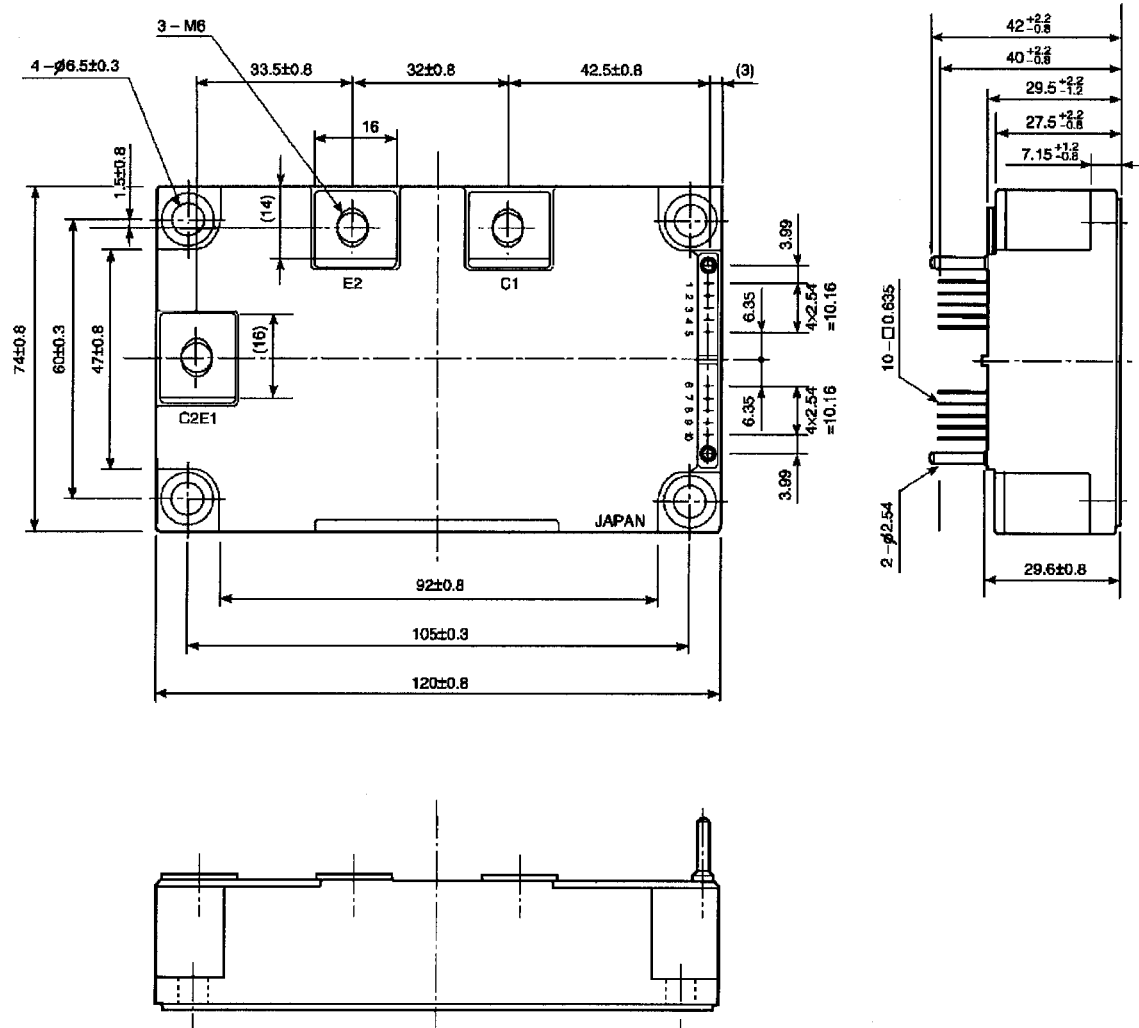






Package Dimensions: TOSHIBA 2-110A1A

Unit: mm



- | | | | | |
|-----------|------------|-----------|---------|------------------------|
| 1. FO (L) | 2. GND (L) | 3. IN (L) | 4. Open | 5. V _D (L) |
| 6. FO (H) | 7. GND (H) | 8. IN (H) | 9. Open | 10. V _D (H) |

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